

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings of claims in the application:

1. (Original) A thin-film EL device having at least a structure comprising an electrically insulating substrate, a patterned electrode layer stacked on said substrate, and a dielectric layer, a light-emitting layer and a transparent electrode stacked on said electrode layer, wherein:

said dielectric layer is a multilayer dielectric layer formed in a multilayer form by repeating a solution coating-and-firing step plural times, and

said multilayer dielectric layer has a thickness of at least four times as large as a thickness of said electrode layer and 4  $\mu\text{m}$  to 16  $\mu\text{m}$  inclusive.

2. (Original) The thin-film EL device according to claim 1, wherein said multilayer dielectric layer is formed by repeating said solution coating-and-firing step at least three times.

3. (Original) The thin-film EL device according to claim 1, wherein said multilayer dielectric layer has a thickness per sub-layer of at least 1/2 of said electrode layer.

4. (Canceled)

5. (Canceled)

6. (Previously Presented) The thin-film EL device according to Claim 1, wherein said electrically insulating substrate maintains a given heat-resistant strength without contaminating said patterned electrode layer and said dielectric layer.

7. (Previously Presented) The thin-film EL device according to Claim 1, wherein said electrically insulating substrate is selected from the group consisting of alumina ( $\text{Al}_2\text{O}_3$ ), quartz glass ( $\text{SiO}_2$ ), magnesia ( $\text{MgO}$ ), forsterite ( $2\text{MgO} \bullet \text{SiO}_2$ ), steatite ( $\text{MgO} \bullet \text{SiO}_2$ ), mullite ( $3\text{Al}_2\text{O}_3 \bullet 2\text{SiO}_2$ ), beryllia ( $\text{BeO}$ ), zirconia ( $\text{ZrO}_2$ ), aluminum nitride ( $\text{AlN}$ ), silicon nitride ( $\text{SiN}$ ), silicon carbide ( $\text{SiC}$ ), crystallized glass, high heat-resistance glass, green sheet glass substrates and enameled metal substrates.

8. (Previously Presented) The thin-film EL device according to Claim 1, wherein said patterned electrode layer has a pattern comprising a plurality of stripes.

9. (Previously Presented) The thin-film EL device according to Claim 8, wherein a line width of said stripes of said patterned electrode is 200 to 500  $\mu\text{m}$  and a space between two stripes is about 20  $\mu\text{m}$ .

10. (Previously Presented) The thin-film EL device according to Claim 1, wherein said patterned electrode layer comprises an oxide conductive material, a base metal, a noble metal, a noble metal alloy and a combination of a noble metal with a nonmetal element.

11. (Previously Presented) The thin-film EL device according to Claim 1, wherein a specific dielectric constant of said dielectric layer is at least 10 times as large as the thickness of the dielectric layer as expressed in  $\mu\text{m}$ .

12. (Previously Presented) The thin-film EL device according to Claim 1, wherein said dielectric layer comprises a material selected from the group consisting of dielectric materials having perovskite structures, composite perovskite-relaxor ferroelectric materials, bismuth layer-structured compounds and tungsten bronze ferroelectric materials.

13. (Previously Presented) The thin-film EL device according to Claim 1, wherein said coating-and-firing process comprises a sol-gel process, an MOD process or a combination thereof.

14. (Canceled)

15. (Previously Presented) The thin-film EL device according to Claim 1, wherein said light-emitting layer comprises ZnS doped with Mn .

16. (Previously Presented) The thin-film EL device according to Claim 1, wherein said light-emitting layer comprises SrS:Ce.

17. (Previously Presented) The thin-film EL device according to Claim 1, wherein said light-emitting layer has a thickness of 100 to 2,000 nm.

18. (Previously Presented) The thin-film EL device according to Claim 1, further comprising an insulator layer disposed on said light-emitting layer.

19. (Previously Presented) The thin-film EL device according to Claim 18, wherein said insulator layer has a thickness of 50 to 1,000 nm.

20. (Previously Presented) The thin-film EL device according to Claim 1, wherein said transparent electrode layer comprises an oxide conductive material.

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**BASIS FOR THE AMENDMENT**

Claim 4 has been canceled.

No new matter is believed to have been added by entry of this amendment. Entry and favorable reconsideration are respectfully requested.

Upon entry of this amendment Claims 1-3, 6-13 and 15-20 will now be active in this application.